Analog Power AM80N06-05D

## N-Channel 60-V (D-S) MOSFET

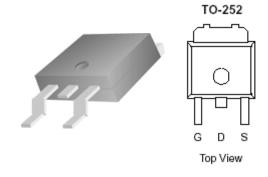
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r <sub>DS(on)</sub> provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

Pb-free	
RoHS	
COMPLIANT	
HALOGEN	
FREE	

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$		
60	$5.9 @ V_{GS} = 10V$	76		
00	$6.6 @ V_{GS} = 4.5V$	72		



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage			60	v
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current <sup>a</sup>	$T_C=25^{\circ}C$	$I_D$	51	A
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	100	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	50	A
Power Dissipation <sup>a</sup>	$T_C=25^{\circ}C$	$P_{\mathrm{D}}$	50	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ heta JA}$	50	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3.0	°C/W		

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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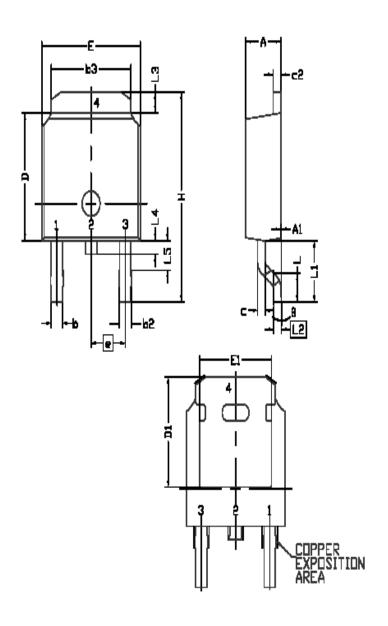
SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Domanoskom	Ch a l	Symbol Test Conditions		Limits		TT
Parameter	Symbol			Тур	Max	Unit
Static	·		•			•
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{\mathrm{DS}} = V_{\mathrm{GS}},  I_{\mathrm{D}} = 250  \mathrm{uA}$	1			V
Gate-Body Leakage	Igss	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	1088	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			A
D : G . C . D : A		$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$			5.9	
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$			6.6	mΩ
Forward Tranconductance <sup>A</sup>	gfs	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		22		S
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 2 A, V_{GS} = 0 V$		1.1		V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 2 \text{ A}$		70		
Gate-Source Charge	$Q_{gs}$			10		nC
Gate-Drain Charge	$Q_{gd}$			30		
Input Capacitance	Ciss	V 15 V V 0 V		5000		
Output Capacitance	Coss	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1MHz		500		pF
Reverse Transfer Capacitance	Crss	= 11/11/12		300		1
Turn-On Delay Time	t <sub>d(on)</sub>			10		
Rise Time	$t_{\rm r}$	$V_{\rm DD} = 25 \ V, \ R_{\rm L} = 25 \ \Omega \ , \ { m ID} = 30 \ A,$ $V_{\rm GEN} = 10 \ V$		20		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			200		
Fall-Time	<b>t</b> f			80		

## Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information



CHMDDI	DIMENS:	iinal i	RECINTS
LOGMY2	MIN	ğ	MAX
E	6.40	6.60	6.731
Г	1.40	1.52	1.77
L1			Ŧ.
L2		508 BS	
L3	0.89		1.27
L4	0.64	I	1.01
L5	1	1	ı
D	6.00	6.10	6,553
Н	9.40	10,00	10.40
ь	0.64	0.76	0.88
<b>5</b> 2	0.77	0.84	1.14
53	5.21	5.34	5.46
•	2.	286 BS	5
Α	2.20	2.30	5'38
A1	0		0.127
С	0.45	0.50	0.60
<u>c</u> 2	0.45	0.50	0.58
DI	5.30	-	-
E	4.40	I	ı
θ	0"		10*

**PRELIMINARY**